

SIDC26D60C8

Fast switching diode chip in Emitter Controlled 3 -Technology

Features:

- 600V Emitter Controlled 3 technology 70 µm chip
- soft, fast switching
- low reverse recovery charge
- small temperature coefficient

This chip is used for:

Power module



Applications:

Drives

Chip Type	V _R	<i>I</i> _F	Die Size	Package
SIDC26D60C8	600V	100A	6.53 x 4.02 mm ²	sawn on foil

Mechanical Parameters

Mechanical Parameters			
Raster size	6.53 x 4.02		
Area total	26.25	mm ²	
Anode pad size	5.83 x 3.32		
Thickness	70	μm	
Wafer size	200	mm	
Max. possible chips per wafer	1032		
Passivation frontside	Photoimide		
Pad metal	3200 nm AlSiCu		
Backside metal	Ni Ag –system suitable for epoxy and soft solder die bonding		
Die bond	Electrically conductive glue or solder		
Wire bond	AI, ≤500μm		
Reject ink dot size	Ø 0.65mm; max 1.2mm		
Recommended storage environment	Store in original container, in dry nitrogen, in dark environment, < 6 month at an ambient temperature of 23°C		



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Maximum Ratings

Parameter	Symbol Condition		Value	Unit	
Repetitive peak reverse voltage	V_{RRM}	<i>T</i> _{vj} = 25 ℃	600	V	
Continuous forward current	I _F	<i>T</i> _{vj} < 150℃	1)	A	
Maximum repetitive forward current	I _{FRM}	<i>T</i> _{vj} < 150℃	200	7 ^	
Junction temperature range	T _{vj}		-40+175	°C	
Operating junction temperature	T _{vj}		-40+150	°C	
Dynamic ruggedness ²⁾	P_{max}	$I_{\text{Fmax}} = 200\text{A}, \ V_{\text{Rmax}} = 600\text{V}, \ T_{\text{vj}} \le 150^{\circ}\text{C}$	tbd	kW	

¹⁾ depending on thermal properties of assembly

Static Characteristics (tested on wafer), $T_{vj} = 25 \text{ }^{\circ}\text{C}$

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	Oilit
Reverse leakage current	I_{R}	V _R =600V			27	μA
Cathode-Anode breakdown Voltage	$V_{\rm BR}$	I _R =0.25mA	600			V
Diode forward voltage	V_{F}	I _F =100A	1.2	1.6	1.9	V

Further Electrical Characteristics

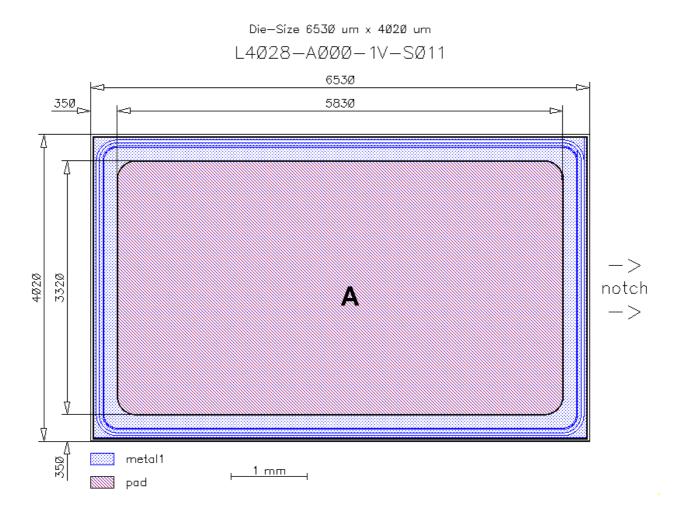
Switching characteristics and thermal properties are depending strongly on module design and mounting technology and can therefore not be specified for a bare die.

²⁾ not subject to production test - verified by design/characterisation





Chip Drawing



A: Anode pad



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Description
AQL 0,65 for visual inspection according to failure catalogue
Electrostatic Discharge Sensitive Device according to MIL-STD 883

Revision History

Version	Subjects (major changes since last revision)	Date

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